

**Amendments to the Claims:**

This listing of the claims will replace all prior versions and listings of claims in the application:

**Listing of Claims:**

Claims 1-5 (canceled)

6 (currently amended): A method of manufacturing a semiconductor device comprising:

the step of forming a capacitor electrode on a semiconductor substrate;

the step of forming an insulating film which has an upper surface on said capacitor electrode;

the step of forming a trench in said insulating film so as to expose part of said capacitor electrode;

the step of forming a conductive material film which fills in the inside of said trench and which extends to the upper surface of said insulating film;

the step of forming a wiring layer which includes said conductive material film which fills in the inside of said trench and which has the upper surface located on a approximately the same plane as the upper surface of said insulating film by removing said conductive material film located on the upper surface of said insulating film and by removing part of said conductive material film located in the trench of said insulating film;

the step of forming a conductive region located below said insulating film; and

the step of forming, in said insulating film, a contact hole which reaches to said conductive region,

wherein said step of forming a trench includes forming another trench in said insulating film in the region located above said contact hole; and

said step of forming a conductive material film includes forming a conductive material film which becomes another wiring layer so as to fill in the inside of said contact hole and said other trench.

7 (canceled)

8 (currently amended): The method of manufacturing a semiconductor device according to claim [[7]] 6, wherein said step of forming a trench includes forming said trench so as to extend approximately in parallel to said other trench.

9 (currently amended): The method of manufacturing a semiconductor device according to claim [[7]] 6, wherein said step of forming a trench includes forming a plurality of aperture parts so as to expose part of said capacitor electrode in said insulating film.

10 (original): The method of manufacturing a semiconductor device according to claim 6, wherein said conductive material film includes copper.